

Title (en)
ELECTROPOLISHING ASSEMBLY AND METHODS FOR ELECTROPOLISHING CONDUCTIVE LAYERS

Title (de)
ELEKTROPOLIERANORDNUNG UND VERFAHREN ZUM ELEKTROPOLIEREN VON LEITFÄHIGEN SCHICHTEN

Title (fr)
ENSEMBLE DE POLISSAGE ELECTROLYTIQUE ET PROCEDES DE POLISSAGE ELECTROLYTIQUE DE COUCHES CONDUCTRICES

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Application
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Abstract (en)

[origin: WO03042433A1] In one aspect of the present invention, an exemplary apparatus and method are provided for electropolishing a conductive film on a wafer 1004. An apparatus includes a wafer chuck 1002 for holding a wafer, an actuator 1000 for rotating the wafer chuck, and a nozzle 1010 configured to electropolish the wafer. The apparatus may further include a conductive ring or a shroud 1006. A method of electropolishing a conductive film on a wafer includes rotating a wafer chuck with sufficient speed such that electrolyte fluid incident upon the wafer flows on the surface of the wafer towards the edge of the wafer.

[origin: WO03042433A1] In one aspect of the present invention, an exemplary apparatus and method are provided for electropolishing a conductive film on a wafer (1004). An apparatus includes a wafer chuck (1002) for holding a wafer, an actuator (1000) for rotating the wafer chuck, and a nozzle (1010) configured to electropolish the wafer. The apparatus may further include a conductive ring or a shroud (1006). A method of electropolishing a conductive film on a wafer includes rotating a wafer chuck with sufficient speed such that electrolyte fluid incident upon the wafer flows on the surface of the wafer towards the edge of the wafer.

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